

Factory Prog. 4 Output CMOS TCXO

- Full Custom Multi-Frequency Programmable Osc
- Reduced EMI by turning off unused output
- Factory Programmable
- Industry-standard packaging saves on board space
- Mult. outputs 1 pkg vs. mult. osc & assoc. comp.
- Performs well under all conditions
- Increased Integration

Applications

- High-end multimedia
- Communications
- Industrial
- A/D converters
- Consumer Applications
- Low tolerance applications
- Low-power applications

Series **CCT4C**

Part Numbering Example: **CCT4C 1A 200.0 / 150.0 / 125.0 / 100.0**

CCT4C	1A	200	150	125	100
SERIES	PACKAGE STYLE	FREQUENCY A	FREQUENCY B	FREQUENCY C	FREQUENCY D
	1A=14 pin dip 9=9.6x11.4 SMD	0.2 - 200 MHz	0.2 - 200 MHz	0.2 - 200 MHz	0.2 - 200 MHz

Specifications:	Min	Typ	Max	Unit
Frequency Range:				
Output A CMOS	0.2		200	MHz
Output B CMOS	0.2		200	MHz
Output C CMOS	0.2		200	MHz
Output D CMOS	0.2		200	MHz
Available Stability Options:	-2.5		2.5	ppm
Supply Voltage:	3.135	3.3	3.465	V
Operating Temperature Range Options:	-40		85	°C
Storage Temperature:	-55		125	°C
Duty Cycle:	40 45		60 55	% %
Start-Up Time:		3	10	mS
Aging (PPM/1st Year): Ta=25C, Vdd=3.3V			±1	ppm
Static Discharge Voltage Mil-Std 883, method 3015	2000			V
Output Load: CMOS, < 40 MHz CMOS, ≥ 40 MHz			30 15	pF pF
Output Level:	CMOS			
Packaging:	25 / Tube Tape & Reel			14 pin SMD

Notes: Recommended .01 µF bypass capacitor from Vcc to GND. Capacitor should be as close to oscillator as possible.



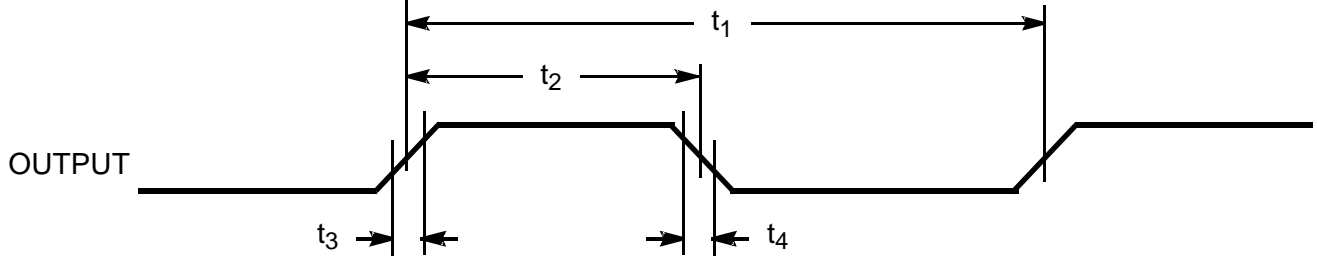
Electrical Characteristics

DESCRIPTION		CONDITIONS	MIN	TYP	MAX	UNIT
Ioh	Output High Current	Voh = (L)Vdd - 0.5, (L)Vdd = 3.3 V	12	24		mA
Iol	Output Low Current	Vol = .5, (L)Vdd = 3.3 V	12	24		mA
Vih	High Level Input Voltage	CMOS levels, % of Vdd	0.7			V
Vil	Low-Level Input Voltage	CMOS levels, % of Vdd			0.3	V
Iih	Input High Current	Vin = AVdd - 0.3 V		<1	10	μA
Iil	Input Low Current	Vin = + 0.3 V		<1	10	μA
Ioz	Output Leakage Current	tri-state outputs			10	μA
Idd	Total Power Supply Current	Example 1: 1 output@19.44 MHz; 1 output@38.88 MHz 1 output@77.76 Mhz; 1 output@155.52 MHz Example 2: 1 output@50 MHz; 1 output@106.25 MHz 1 output@200 Mhz; 1 output@155.52 MHz		26		mA
				38		mA
Idds	Shutdown Power Supply Curr	Shutdown active		5	20	μA

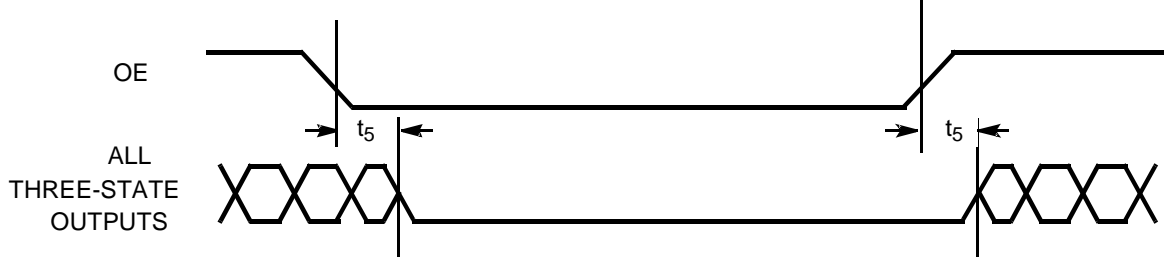
Output Clock Switching Characteristics

DESCRIPTION		CONDITIONS	MIN	TYP	MAX	UNIT
1/t1	Output Frequency	Clock output limit, CMOS, Commercial			200	MHz
t3	Rising Edge Slew Rate	Output clock rise time, 20% – 80% Vdd	0.75	1.4		nS
t4	Falling Edge Slew Rate	Output clock fall time, 20% – 80% Vdd	0.75	1.4		nS
t5	Output tri-state timing after SD/OE switches	Time for output to enter/leave tri-state mode		150	300	nS
t6	Clock Jitter measured at Vdd/2	Peak-to-Peak period jitter, CLK outputs		200		pS

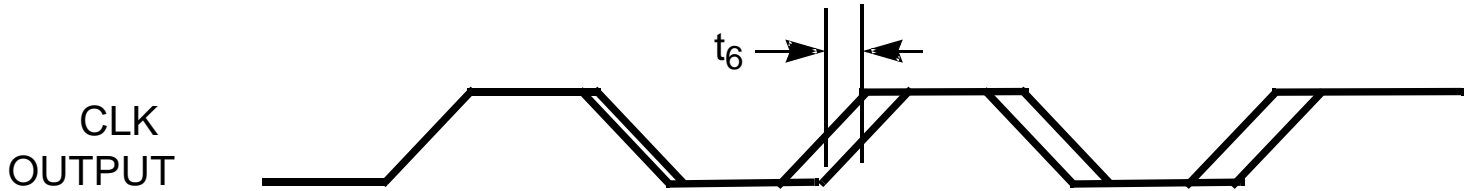
ALL OUTPUTS, DUTY CYCLE, RISE/FALL TIME



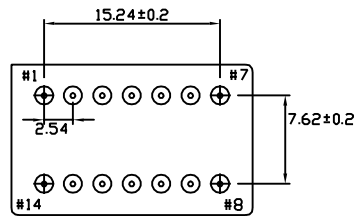
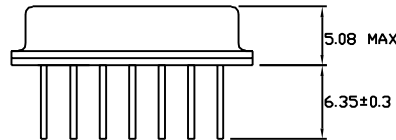
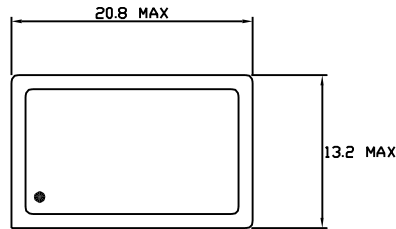
OUTPUT 3-STATE TIMING



CLK OUTPUT JITTER



DIP

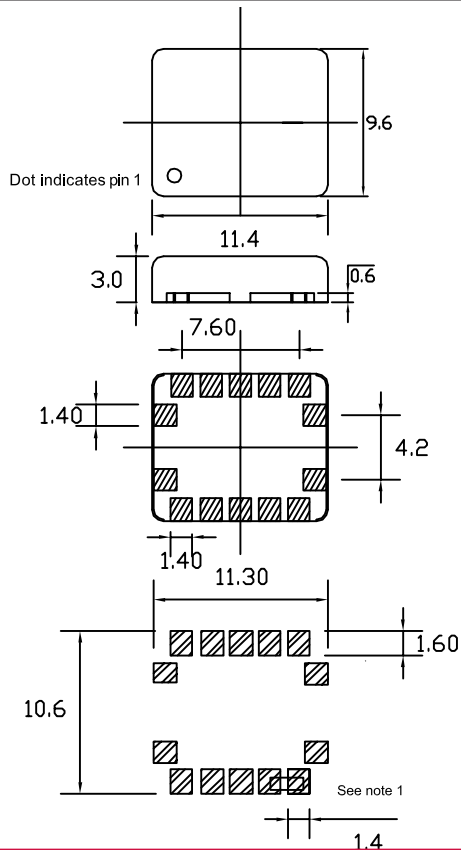


Dimensions are in mm

PIN FUNCTION

- PIN 1 OE (CONNECT TO VDD)
- PIN 2 SUSPEND (CONNECT TO GND)
- PIN 3 VDD
- PIN 4 CLK C OUTPUT
- PIN 5 CONNECT TO PIN 6
- PIN 6 CONNECT TO PIN 5
- PIN 7 GND
- PIN 8 FACTORY USE (MAKE NO CONNECTION)
- PIN 9 CLK D OUTPUT
- PIN10 FACTORY USE (MAKE NO CONNECTION)
- PIN 11 FACTORY USE (MAKE NO CONNECTION)
- PIN 12 FACTORY USE (MAKE NO CONNECTION)
- PIN 13 CLK A OUTPUT
- PIN 14 CLK B OUTPUT

SMD



PIN FUNCTION

- PIN 1 FACTORY USE (MAKE NO CONNECTION)
- PIN 2 OE
- PIN 3 VDD
- PIN 4 CLK C OUTPUT
- PIN 5 CONNECT TO PIN 6
- PIN 6 CONNECT TO PIN 5
- PIN 7 GND
- PIN 8 FACTORY USE (MAKE NO CONNECTION)
- PIN 9 CLK D OUTPUT
- PIN10 FACTORY USE (MAKE NO CONNECTION)
- PIN 11 FACTORY USE (MAKE NO CONNECTION)
- PIN 12 FACTORY USE (MAKE NO CONNECTION)
- PIN 13 CLK A OUTPUT
- PIN 14 CLK B OUTPUT

Dimensions in mm
Recommended solder pad layout

Note1:
For proper operation pin 5 must be connected to pin 6

